

NTHD4N02F

Power MOSFET and Schottky Diode

20 V, 2.7 A, N-Channel, with 1.0 A Schottky Barrier Diode, ChipFET

Features

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP-6 Package with Better Thermals
- Super Low Gate Charge MOSFET
- Ultra Low V_F Schottky
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

Applications

- Fast Switching, low Gate Charge for Dc to Dc Buck and Boost Converters
- Li-Ion Battery Applications in Cell Phones, PDAs, DSCs, and Media Players
- Load Side Switching

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	± 12	V
Continuous Drain Current	Steady State	$T_J=25^{\circ}\text{C}$	I_D	2.7	A
		$T_J=85^{\circ}\text{C}$		1.7	
Pulsed Drain Current	$t_p=10\text{ }\mu\text{s}$		I_{DM}	9.0	A
Power Dissipation	Steady State	$T_J=25^{\circ}\text{C}$	P_D	0.91	W
		$T_J=85^{\circ}\text{C}$		0.36	
Continuous Source Current (Body Diode)			I_S	2.7	A
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 125	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

SCHOTTKY DIODE MAXIMUM RATINGS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R	20	V
Average Rectified Forward Current	I_F	2.2	A

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	110	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5 \text{ s}$	$R_{\theta JA}$	60	$^\circ\text{C/W}$

1. Surface Mounted on FR4 Board using 1 in sq. pad size (Cu area = 1.27 in sq. [1 oz] including traces).



ON Semiconductor®

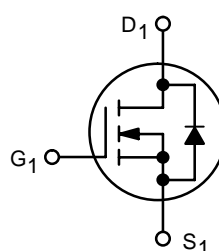
<http://onsemi.com>

MOSFET

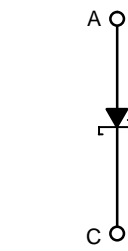
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
20 V	60 m Ω @ 4.5 V	2.7 A
	80 m Ω @ 2.5 V	

SCHOTTKY DIODE

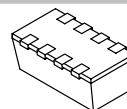
V_R MAX	V_F TYP	I_F MAX
20 V	0.35 V	1.0 A



N-Channel MOSFET

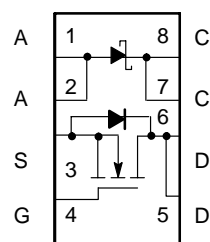


SCHOTTKY DIODE



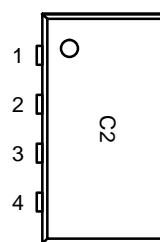
ChipFET™
CASE 1206A
STYLE 3

PIN CONNECTIONS



(Top View)

MARKING DIAGRAM



C2 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
NTHD4N02FT1	ChipFET	3000/Tape & Reel
NTHD4N02FT1G	ChipFET (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTHD4N02F

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
-----------	--------	-----------------	-----	-----	-----	-------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20	28		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V V _{DS} = 16 V	T _J = 25°C T _J = 85°C		1.0 5.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.6		1.2	V
Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 2.7 A V _{GS} = 2.5 V, I _D = 2.3 A		0.058 0.077	0.080 0.115	Ω
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 2.7 A		6.0		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V		180	300	pF
Output Capacitance	C _{OSS}			80	130	
Reverse Transfer Capacitance	C _{RSS}			30	50	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 2.7 A		2.6	4.0	nC
Gate-to-Source Charge	Q _{GS}			0.6		
Gate-to-Drain Charge	Q _{GD}			0.7		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 16 V, I _D = 2.7 A, R _G = 2.5 Ω		5.0	10	ns
Rise Time	t _r			9.0	18	
Turn-Off Delay Time	t _{d(OFF)}			10	20	
Fall Time	t _f			3.0	6.0	

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 2)

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 2.7 A		0.8	1.15	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _S = 2.7 A, dI _S /dt = 100 A/μs		12.5		ns
Charge Time	t _a			9.0		
Discharge Time	t _b			3.5		
Reverse Recovery Charge	Q _{RR}			6.0		nC

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Maximum Instantaneous Forward Voltage	V _F	I _F = 0.1 A I _F = 1.0 A			0.31 0.365	V
Maximum Instantaneous Reverse Current	I _R	V _R = 10 V V _R = 20 V			0.75 2.5	mA
Non-Repetitive Peak Surge Current	I _{FSM}	Halfwave, Single Pulse, 60 Hz			23	A

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL MOSFET PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

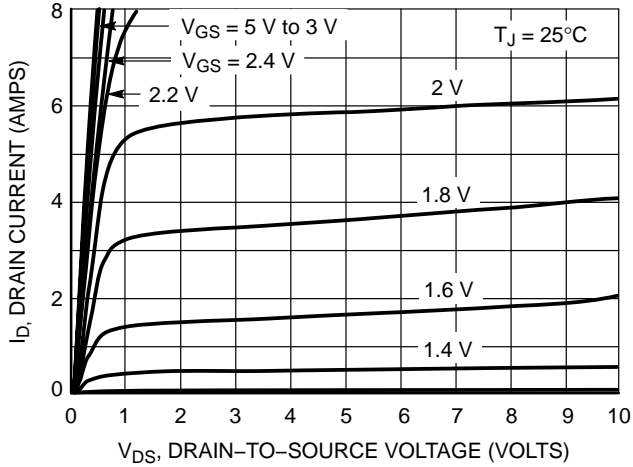


Figure 1. On-Region Characteristics

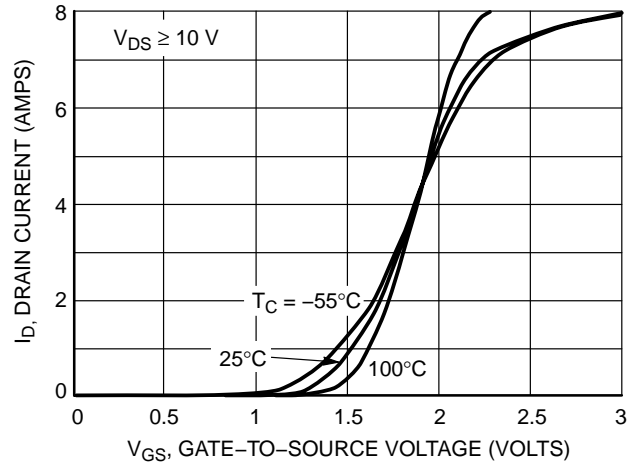


Figure 2. Transfer Characteristics

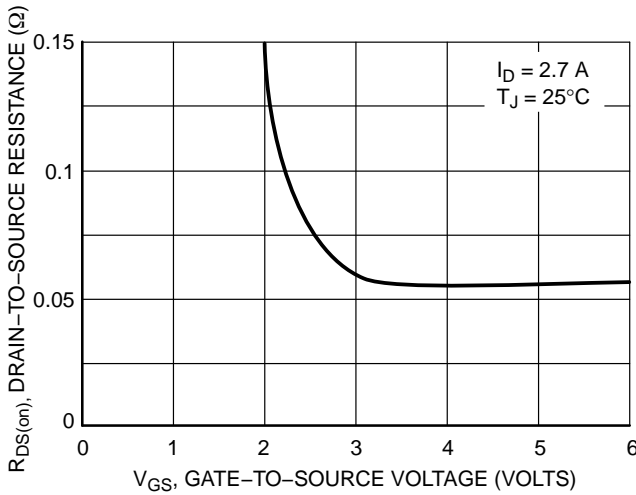


Figure 3. On-Resistance vs. Gate-to-Source Voltage

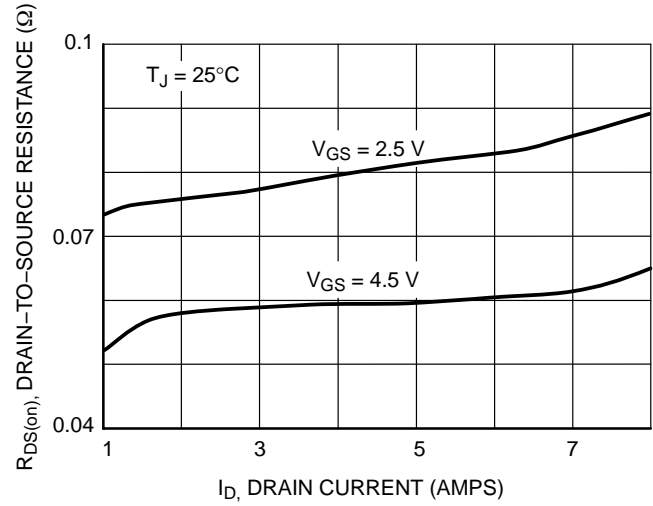


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

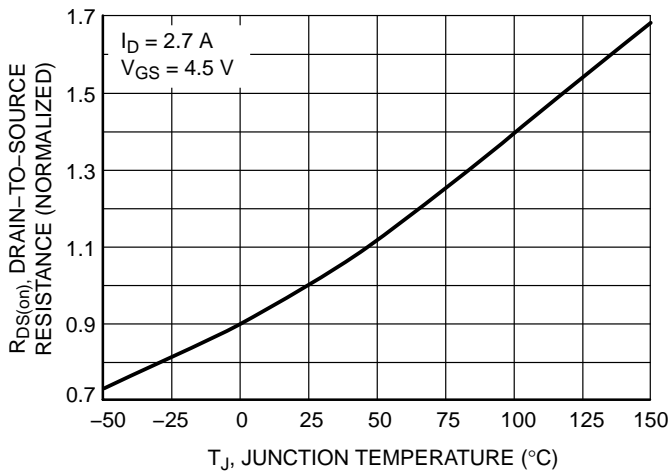


Figure 5. On-Resistance Variation with Temperature

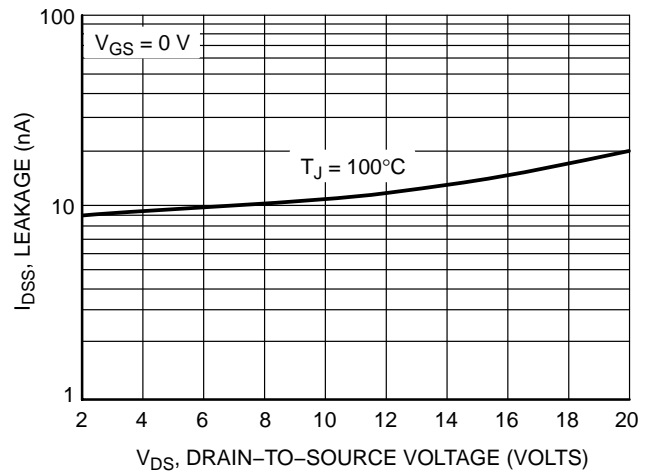


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL MOSFET PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

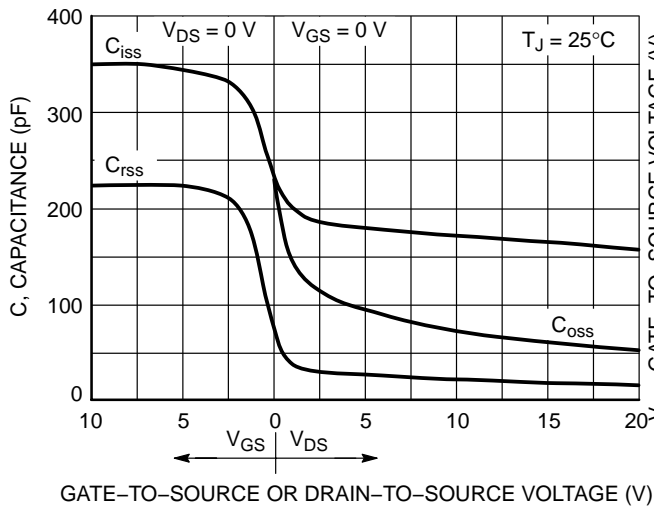


Figure 7. Capacitance Variation

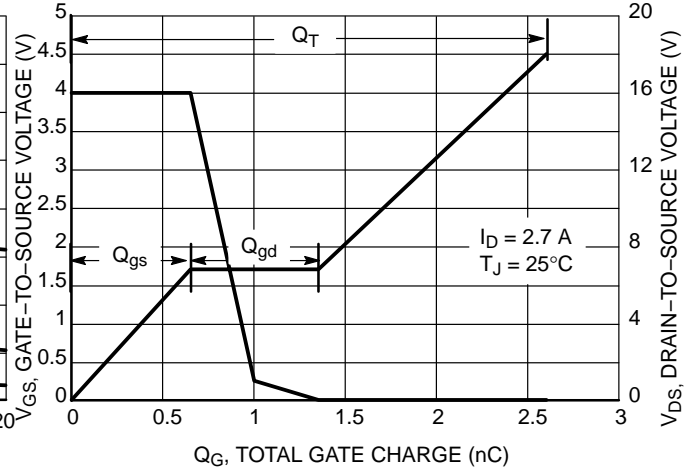


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

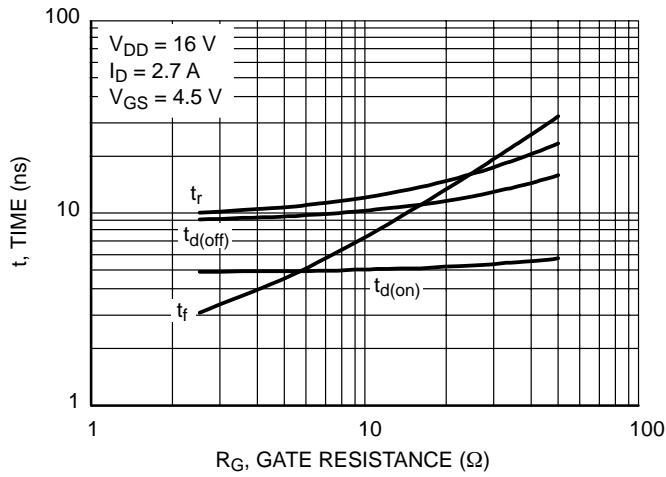


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

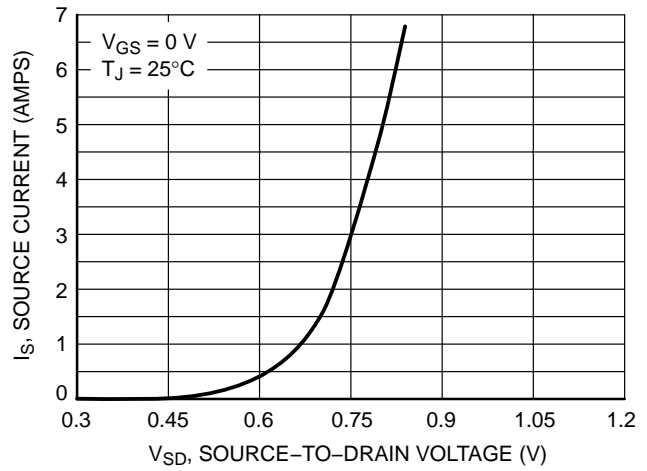


Figure 10. Diode Forward Voltage vs. Current

TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

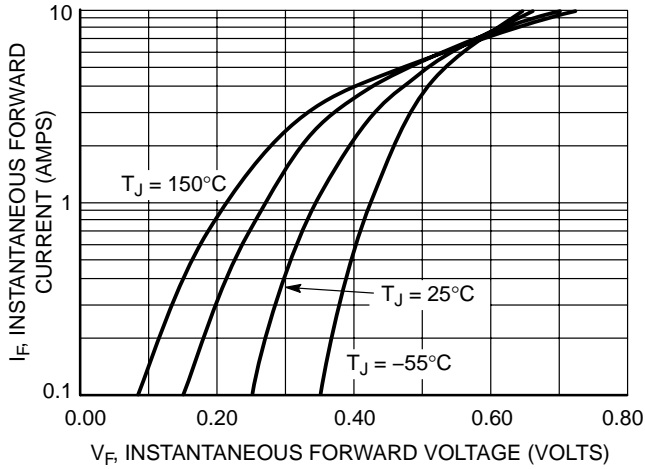


Figure 11. Typical Forward Voltage

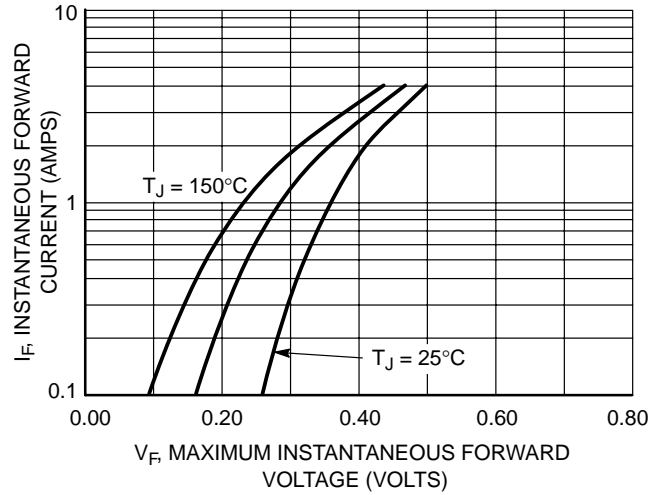


Figure 12. Maximum Forward Voltage

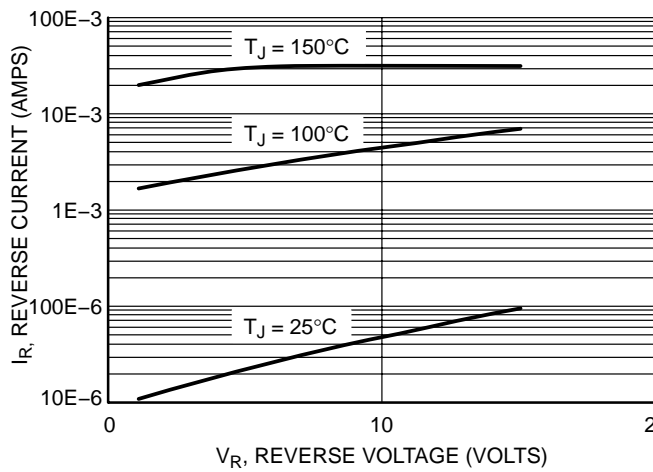


Figure 13. Typical Reverse Current

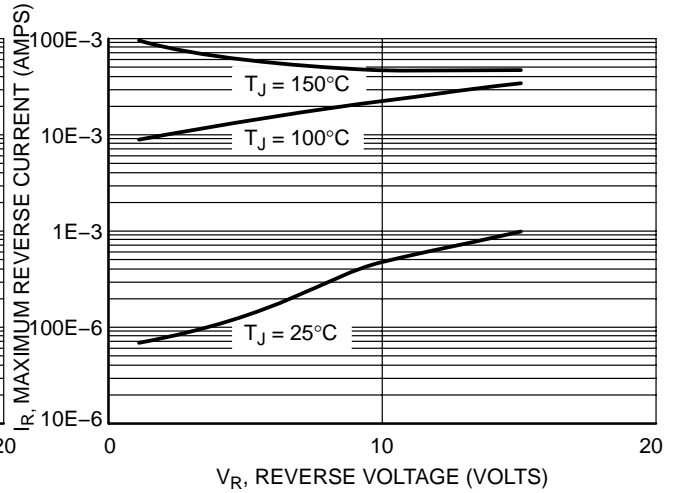


Figure 14. Maximum Reverse Current

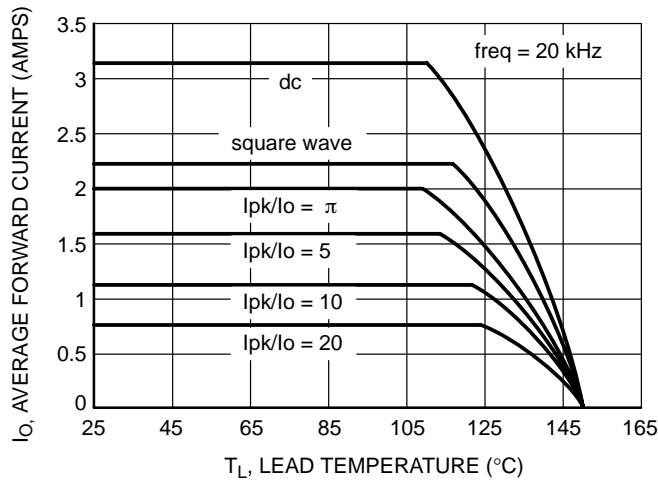


Figure 15. Current Derating

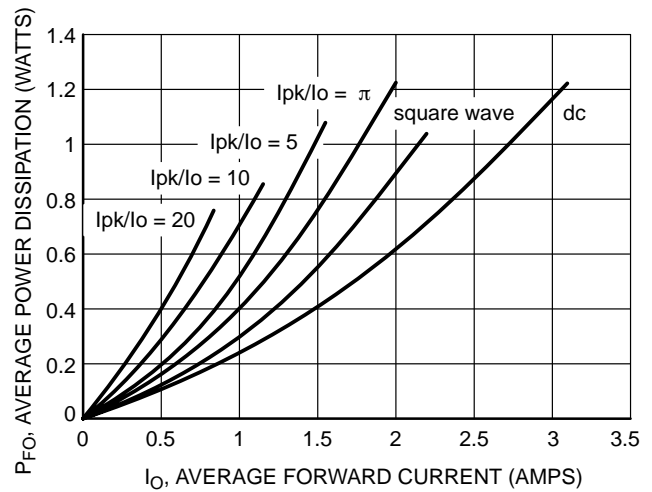
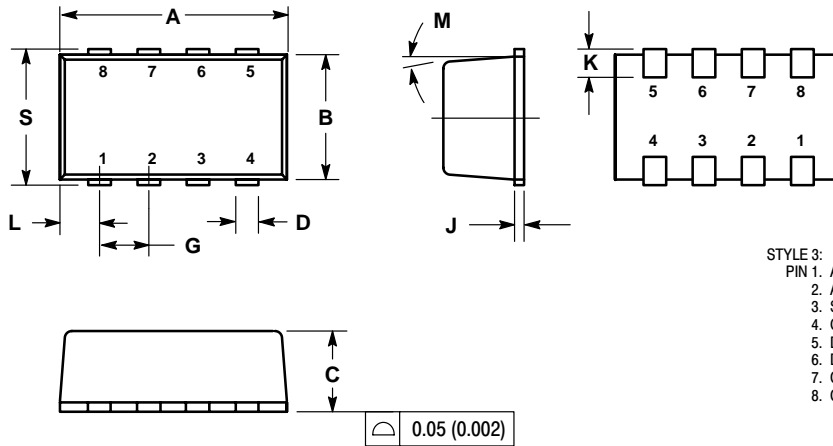


Figure 16. Forward Power Dissipation

NTHD4N02F

PACKAGE DIMENSIONS

ChipFET CASE 1206A-03 ISSUE E



STYLE 3:
PIN 1. A
2. A
3. S
4. G
5. D
6. D
7. C
8. C

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
 4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
 5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
 6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.
 7. 1206A-01 AND 1206A-02 OBSOLETE. NEW STANDARD IS 1206A-03.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.95	3.10	0.116	0.122
B	1.55	1.70	0.061	0.067
C	1.00	1.10	0.039	0.043
D	0.25	0.35	0.010	0.014
G	0.65 BSC		0.025 BSC	
J	0.10	0.20	0.004	0.008
K	0.28	0.42	0.011	0.017
L	0.55 BSC		0.022 BSC	
M	5° NOM		5° NOM	
S	1.80	2.00	0.072	0.080

SOLDER FOOTPRINTS*

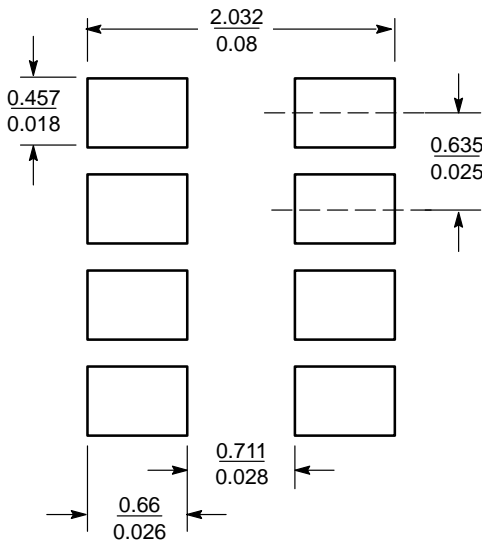


Figure 17. Basic

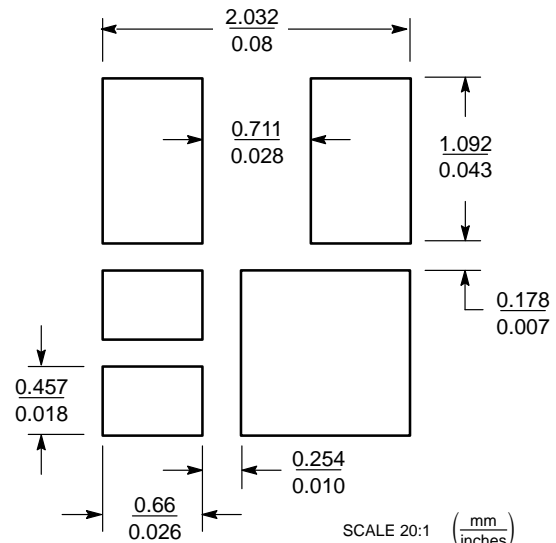



Figure 18. Style 3

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

ChipFET is a trademark of Vishay Siliconix.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.

NTHD4N02F/D